

S1A - S1M

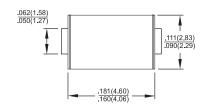


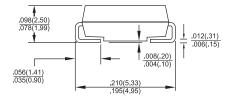
1.0 AMP. Surface Mount Rectifiers **SMA/DO-214AC**



Features

- ♦ For surface mounted application
- ♦ Glass passivated junction chip.
- ♦ Low forward voltage drop
- ♦ High current capability
- ♦ Easy pick and place
- ♦ High surge current capability
- Plastic material used carries Underwriters Laboratory Classification 94V-0
- High temperature soldering:
 260°C / 10 seconds at terminals
- High reliability grade (AEC Q101 qualified)





Mechanical Data

- ♦ Case: Molded plastic
- Terminals: Pure tin plated, lead free solderable per J-STD-002B and JESD22-B102D.
- ♦ Polarity: Indicated by cathode band
- Packaging: 12mm tape per EIA STD RS-481
- ♦ Weight: 0.064 gram

Dimensions in inches and (millimeters)

Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.

Single phase, half wave, 60 Hz, resistive or inductive load.

For capacitive load, derate current by 20%

Type Number	Symbol	S1A	S1B	S1D	S1G	S1J	S1K	S1M	Units
Maximum Recurrent Peak Reverse Voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS Voltage	V _{RMS}	35	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	V_{DC}	50	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current @T _L =110 °C	I _(AV)	1.0							Α
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method)	I _{FSM}	40 30							Α
Maximum Instantaneous Forward Voltage @ 1.0A	V_{F}	1.1							V
Maximum DC Reverse Current @ $T_A = 25$ °C at Rated DC Blocking Voltage @ $T_A = 125$ °C	I _R	1.0 50							uA uA
Typical Reverse Recovery Time (Note 1)	Trr	1.5							uS
Typical Junction Capacitance (Note 2)	Cj	12							pF
Non-Repetitive Peak Reverse Avalanche Engergy at 25°C, I _{AS} =1A, L=10mH	E _{AS}	5							mJ
Typical Thermal Resistance (Note 3)	$R_{ hetaJL}$ $R_{ hetaJA}$			27 75				0 5	°C/W
Operating Temperature Range	TJ	-55 to +150							°C
Storage Temperature Range	Tstg	-55 to +150							°C

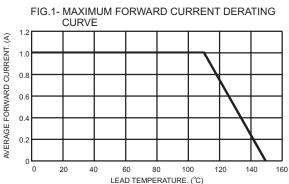
Notes:

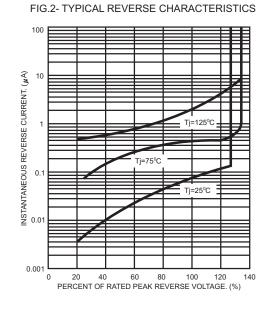
- 1. Reverse Recovery Test Conditions: I_F =0.5A, I_R =1.0A, I_{RR} =0.25A
- 2. Measured at 1 MHz and Applied V_R=4.0 Volts
- 3. Measured on P.C. Board with 0.2" x 0.2" (5.0mm x 5.0mm) Copper Pad Areas.

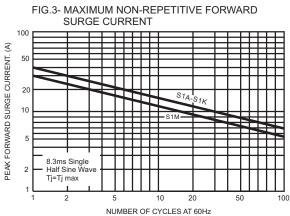
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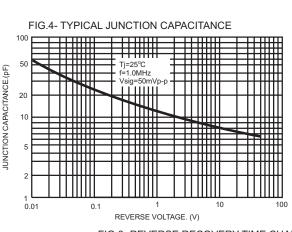


RATINGS AND CHARACTERISTIC CURVES (S1A THRU S1M)









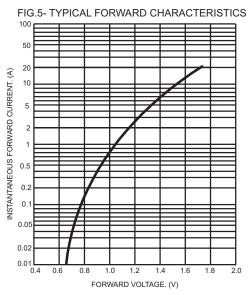
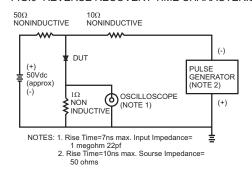
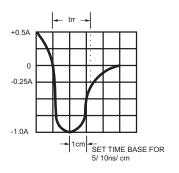


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM





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